# Dual General Purpose Transistor

The NST3906DXV6T1 device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-563 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

- h<sub>FE</sub>, 100-300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Lead-Free Solder Plating

#### MAXIMUM RATINGS

| Rating                         | Symbol           | Value                 | Unit |
|--------------------------------|------------------|-----------------------|------|
| Collector - Emitter Voltage    | V <sub>CEO</sub> | -40                   | Vdc  |
| Collector - Base Voltage       | V <sub>CBO</sub> | -40                   | Vdc  |
| Emitter - Base Voltage         | V <sub>EBO</sub> | -5.0                  | Vdc  |
| Collector Current - Continuous | Ι <sub>C</sub>   | -200                  | mAdc |
| Electrostatic Discharge        | ESD              | HBM>16000,<br>MM>2000 | V    |

#### THERMAL CHARACTERISTICS

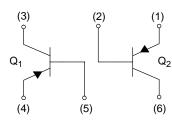
| Characteristic<br>(One Junction Heated)                     |        | Symbol         | Мах                                       | Unit        |
|---|--------|----------------|---|-------------|
| Total Device Dissipation T <sub>A</sub> =                   | = 25°C | PD             | 357                                       | mW          |
| Derate above 25°C   |        |                | (Note 1)<br>2.9<br>(Note 1)               | mW/°C       |
| Thermal Resistance<br>Junction-to-Ambient                   |        | $R_{\thetaJA}$ | 350<br>(Note 1)                           | °C/W        |
| Characteristic  |        |                |   |             |
| (Both Junctions Heated)                                     |        | Symbol         | Max                                       | Unit        |
| (Doni ounono noucou)  |        | Symbol         | IVIAX                                     | Unit        |
|   | = 25°C | P <sub>D</sub> | 500                                       | mW          |
|   |        |                |   |             |
| Total Device Dissipation $T_A =$                            |        |                | 500<br>(Note 1)<br>4.0                    | mW          |
| Total Device Dissipation T <sub>A</sub> = Derate above 25°C |        | P <sub>D</sub> | 500<br>(Note 1)<br>4.0<br>(Note 1)<br>250 | mW<br>mW/°C |

1. FR-4 @ Minimum Pad



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NST3906DXV6T1



CASE 463A PLASTIC

#### MARKING DIAGRAM



A2 = Specific Device Code D = Date Code

#### **ORDERING INFORMATION**

| Device        | Package | Shipping                       |
|---------------|---------|--------------------------------|
| NST3906DXV6T1 | SOT-563 | 4 mm pitch<br>4000/Tape & Reel |
| NST3906DXV6T5 | SOT-563 | 2 mm pitch<br>8000/Tape & Reel |

Semiconductor Components Industries, LLC, 2003 March, 2003 - Rev. 0

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic                                 | Symbol               | Min  | Max | Unit |
|--|----------------------|------|-----|------|
| OFF CHARACTERISTICS                            |                      |      |     |      |
| Collector - Emitter Breakdown Voltage (Note 2) | V <sub>(BR)CEO</sub> | -40  | -   | Vdc  |
| Collector - Base Breakdown Voltage             | V <sub>(BR)CBO</sub> | -40  | -   | Vdc  |
| Emitter - Base Breakdown Voltage               | V <sub>(BR)EBO</sub> | -5.0 | -   | Vdc  |
| Base Cutoff Current                            | I <sub>BL</sub>      | -    | -50 | nAdc |
| Collector Cutoff Current                       | I <sub>CEX</sub>     | -    | -50 | nAdc |

#### ON CHARACTERISTICS (Note 2)

| $ \begin{array}{l} \mbox{DC Current Gain} \\ (I_C = -0.1 \mbox{ mAdc}, V_{CE} = -1.0 \mbox{ Vdc}) \\ (I_C = -1.0 \mbox{ mAdc}, V_{CE} = -1.0 \mbox{ Vdc}) \\ (I_C = -10 \mbox{ mAdc}, V_{CE} = -1.0 \mbox{ Vdc}) \\ (I_C = -50 \mbox{ mAdc}, V_{CE} = -1.0 \mbox{ Vdc}) \\ (I_C = -100 \mbox{ mAdc}, V_{CE} = -1.0 \mbox{ Vdc}) \\ \end{array} $ | h <sub>FE</sub>      | 60<br>80<br>100<br>60<br>30 | -<br>-<br>300<br>- | -   |
|--|----------------------|-----------------------------|--------------------|-----|
| Collector - Emitter Saturation Voltage<br>( $I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$ )<br>( $I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$ )   | V <sub>CE(sat)</sub> | -                           | -0.25<br>-0.4      | Vdc |
| Base - Emitter Saturation Voltage<br>$(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$<br>$(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$  | V <sub>BE(sat)</sub> | -0.65<br>-                  | -0.85<br>-0.95     | Vdc |

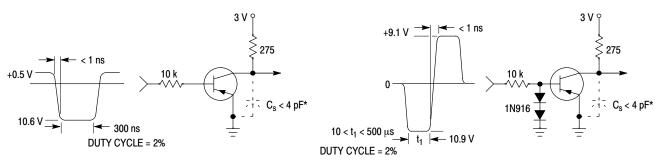
#### SMALL- SIGNAL CHARACTERISTICS

| Current - Gain - Bandwidth Product  | f <sub>T</sub>   | 250 | -    | MHz                 |
|---|------------------|-----|------|---------------------|
| Output Capacitance  | C <sub>obo</sub> | -   | 4.5  | pF                  |
| Input Capacitance   | C <sub>ibo</sub> | -   | 10.0 | pF                  |
| Input Impedance<br>(V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)                         | h <sub>ie</sub>  | 2.0 | 12   | kΩ                  |
| Voltage Feedback Ratio<br>(V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)                  | h <sub>re</sub>  | 0.1 | 10   | X 10 <sup>- 4</sup> |
| Small- Signal Current Gain<br>(V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)              | h <sub>fe</sub>  | 100 | 400  | -                   |
| Output Admittance<br>(V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)                       | h <sub>oe</sub>  | 3.0 | 60   | μmhos               |
| Noise Figure<br>(V <sub>CE</sub> = -5.0 Vdc, I <sub>C</sub> = -100 μAdc, R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz) | NF               | -   | 4.0  | dB                  |

#### SWITCHING CHARACTERISTICS

| Delay Time   | (V <sub>CC</sub> = -3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc)  | t <sub>d</sub> | - | 35  |    |
|--------------|--|----------------|---|-----|----|
| Rise Time    | (I <sub>C</sub> = -10 mAdc, I <sub>B1</sub> = -1.0 mAdc) | t <sub>r</sub> | - | 35  | ns |
| Storage Time | $(V_{CC} = -3.0 \text{ Vdc}, I_C = -10 \text{ mAdc})$    | t <sub>s</sub> | - | 225 |    |
| Fall Time    | (I <sub>B1</sub> = I <sub>B2</sub> = -1.0 mAdc)          | t <sub>f</sub> | - | 75  | ns |

2. Pulse Test: Pulse Width  $\leq$  300 µs; Duty Cycle  $\leq$  2.0%.



\* Total shunt capacitance of test jig and connectors

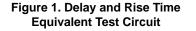
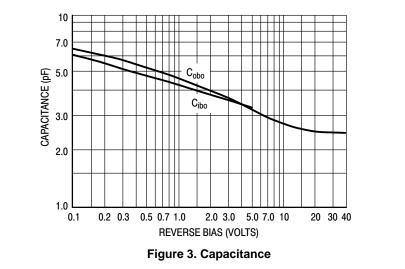
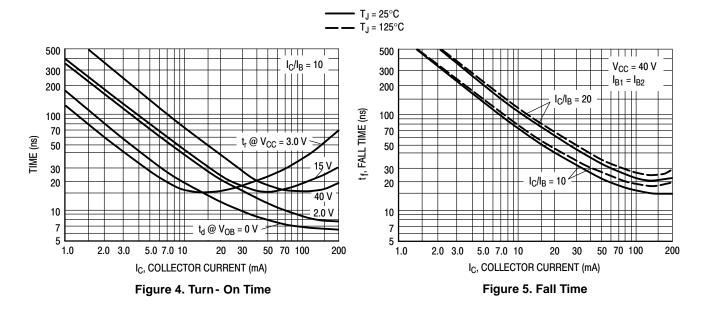


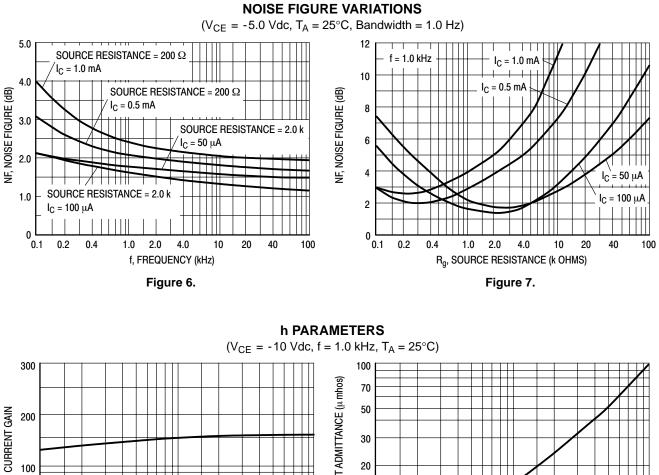
Figure 2. Storage and Fall Time Equivalent Test Circuit

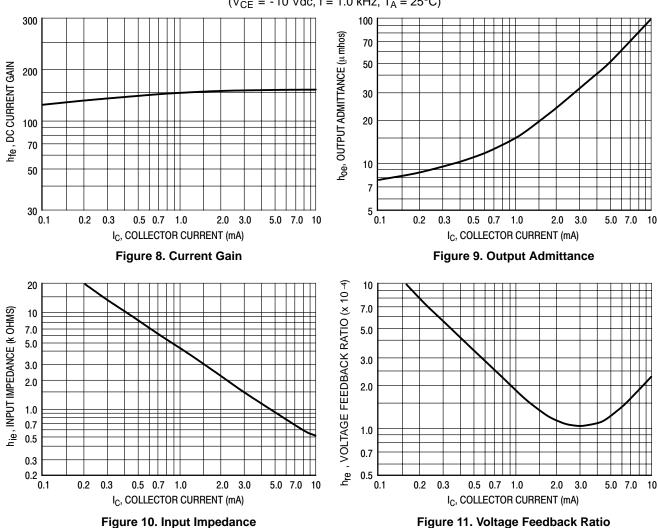




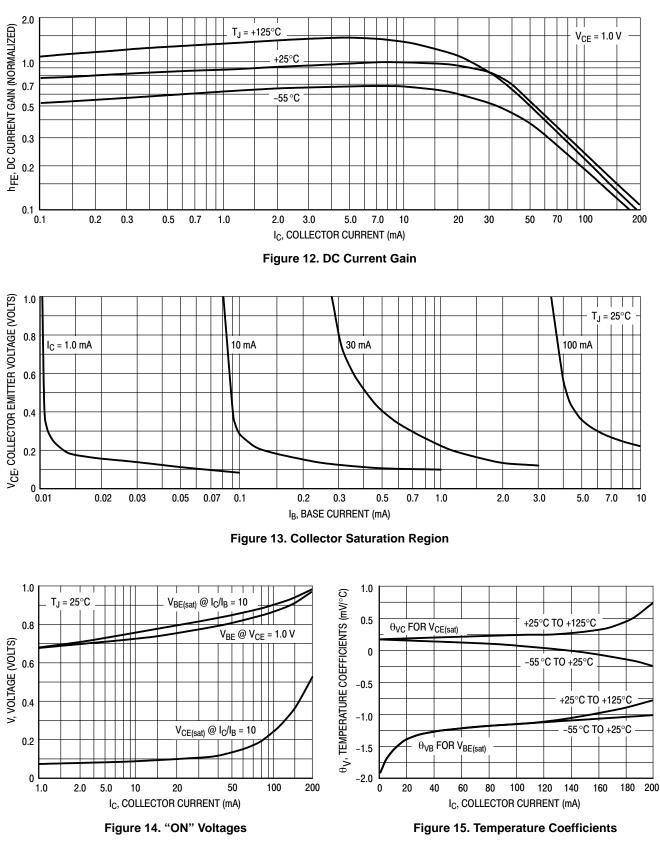


**TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS** 





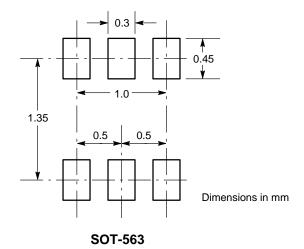
#### **TYPICAL STATIC CHARACTERISTICS**



## INFORMATION FOR USING THE SOT-563 SURFACE MOUNT PACKAGE MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.





The power dissipation of the SOT-563 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient, and the operating temperature,  $T_A$ . Using the values provided on the data sheet for the SOT-563 package,  $P_D$  can be calculated as follows:

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 150 milliwatts.

$$P_{D} = \frac{150^{\circ}C - 25^{\circ}C}{833^{\circ}C/W} = 150 \text{ milliwatts}$$

The 833°C/W for the SOT-563 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 150 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT-563 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad<sup>®</sup>. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

#### SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device

Thermal Clad is a registered trademark of the Bergquist Company.



#### SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A ISSUE J DATE 15 FEB 2024 NOTES: 1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018. 2. ALL DIMENSION ARE IN MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM 3 THICKNESS OF BASE MATERIAL. -A D MILLIMETERS А 6X L DIM В MIN NDM. MAX. m 0.50 0.55 А 0.60 ł 6 4 PIN b 0.17 0.22 0.27 F Н REFERENCE $\subset$ 0.08 0.13 0.18 2 ັບ 1 3 D 1.50 1.60 1.70 E 1.20 1.30 1.10 -⊨ 6X b C ⊕ 0.08∭ A B е 0.50 BSC е Н 1.50 1.60 1.70 TOP VIEW SIDE VIEW L 0.10 0.20 0.30 1.30 6X 0.45 0.30 1.80 STYLE 1: STYLE 2 STYLE 3 PIN 1. EMITTER 1 2. BASE 1 PIN 1. EMITTER 1 PIN 1. CATHODE 1 2. CATHODE 1 2. EMITTER 2 3. COLLECTOR 2 3. BASE 2 3. ANDDE/ANDDE 2 4. EMITTER 2 4. COLLECTOR 2 4. CATHODE 2 0.50 5. BASE 2 5. BASE 1 5. CATHODE 2 6. COLLECTOR 1 PITCH 6. COLLECTOR 1 6. ANDDE/ANDDE 1 RECOMMENDED MOUNTING FOOTPRINT\* STYLE 6: PIN 1. CATHODE 2. ANODE FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE STYLE 5 STYLE 4: 1. CATHODE 2. CATHODE PIN 1. COLLECTOR PIN 2. COLLECTOR 3. BASE 3. ANDDE 3. CATHODE 4. ANDDE 5. CATHODE 4. CATHODE 5. CATHODE 4. EMITTER MANUAL, SOLDERRM/D. 5, COLLECTOR 6. COLLECTOR 6. CATHODE 6. CATHODE GENERIC **MARKING DIAGRAM\*** STYLE 7: STYLE 8 STYLE 9 PIN 1. CATHODE PIN 1. DRAIN PIN 1. SOURCE 1 2. ANDDE 2. DRAIN 2. GATE 1 XXM. 3. CATHODE 4. CATHODE 3. GATE 4. SDURCE 5. DRAIN 3. DRAIN 2 4. SDURCE 2 5. GATE 2 1 5. ANDDE 6. CATHODE 6. DRAIN 6. DRAIN 1 XX = Specific Device Code M = Month Code = Pb-Free Package STYLE 10: STYLE 11: \*This information is generic. Please refer to PIN 1. CATHODE 1 PIN 1. EMITTER 2 device data sheet for actual part marking. 2. N/C 3. CATHODE 2 2. BASE 2 3. COLLECTOR 1 Pb-Free indicator, "G" or microdot "•", may 4. ANDDE 2 EMITTER 1 4. or may not be present. Some products may BASE 5. N/C 5. not follow the Generic Marking. 6. ANDDE 1 COLLECTOR 2 6. Electronic versions are uncontrolled except when accessed directly from the Document Repository. **DOCUMENT NUMBER:** 98AON11126D Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SOT-563-6 1.60x1.20x0.55, 0.50P PAGE 1 OF 1

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